★ Super Low Gate Charge
★ 100% EAS Guaranteed
★ Green Device Available
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

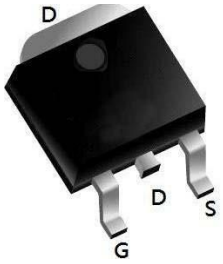
Product Summary

BVDSS	RDSON	ID
30V	15mΩ	20A

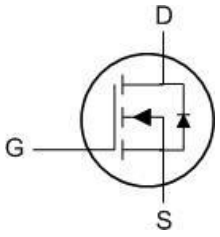
Description

The ZX 20N03 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.
The ZX 20N03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration



pin assignment



Schematic diagram

Package Marking and Ordering Information

Product	Package	Marking	Packing	Min Unit Quantity
ZX 2302A	SOT23	*	3000PCS/Reel	3000PCS

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	±20		V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	20		A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	8		A
I_{DM}	Pulsed Drain Current[2]	38		A
EAS	Single Pulse Avalanche Energy[3]	28		mJ
I_{AS}	Avalanche Current	13.8		A
P_D@T_C=25℃	Total Power Dissipation[4]	5.5		W
T_{STG}	Storage Temperature Range	-55 to 175		℃
T_J	Operating Junction Temperature Range	-55 to 175		℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	36	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS} = 0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=5A	-	15	20	mΩ
		V_{GS}=4.5V, I_D=3A	-	21	29	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1.0MHz	-	490	-	pF
C_{oss}	Output Capacitance		-	79	-	pF
C_{rss}	Reverse Transfer Capacitance		-	61	-	pF
Q_g	Total Gate Charge	V_{DS}=15V, I_D=5.8A, V_{GS}=10V	-	10	-	nC
Q_{gs}	Gate-Source Charge		-	1.7	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	2.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V, I_D=3A, V_{GS}=10V, R_{REN} =3Ω	-	6	-	ns
t_r	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	17	-	ns
t_f	Turn-off Fall Time		-	17	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	9	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	36	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=9A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=5A, dI/dt=100A/μs	-	7	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	2	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25℃,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25Ω,I_{AS}=6A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

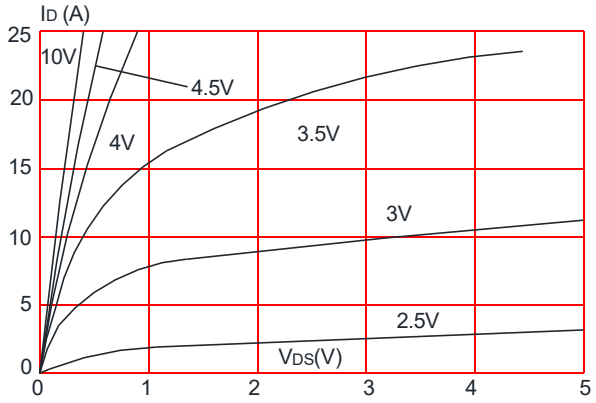


Figure 2: Typical Transfer Characteristics

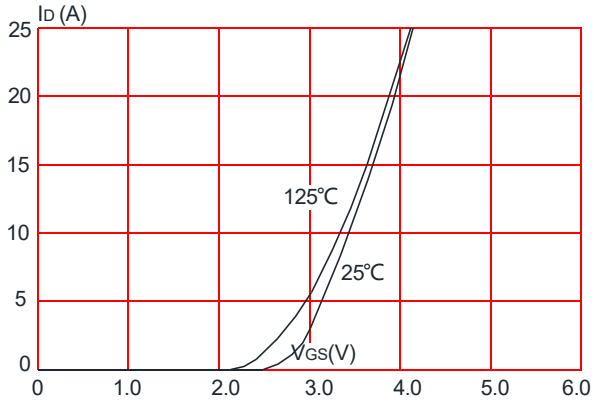


Figure 3: On-resistance vs. Drain Current

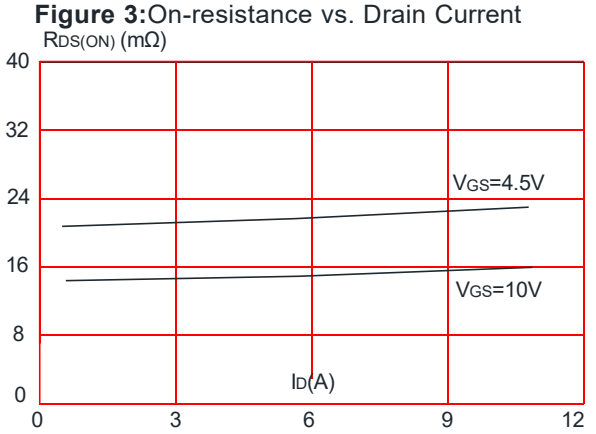


Figure 4: Body Diode Characteristics

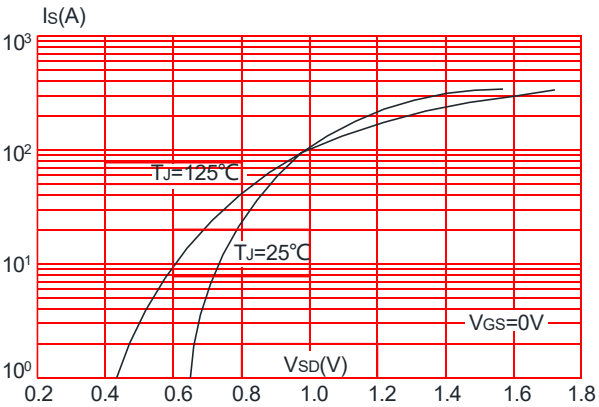


Figure 5: Gate Charge Characteristics

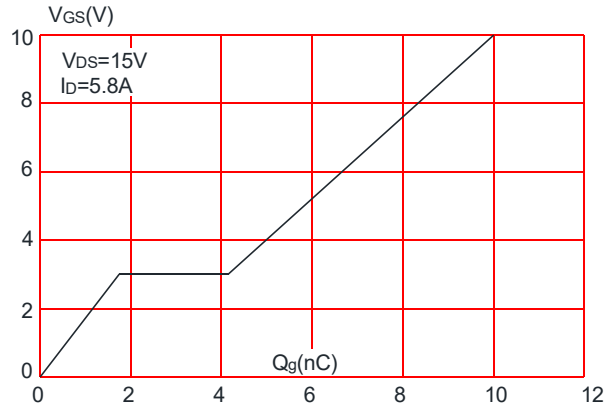


Figure 6: Capacitance Characteristics

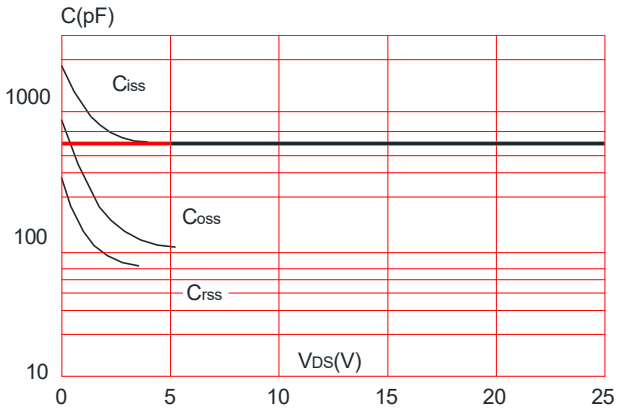


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

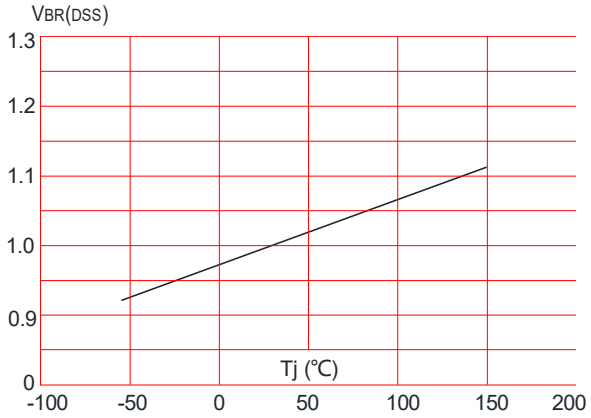


Figure 8: Normalized on Resistance vs. Junction Temperature

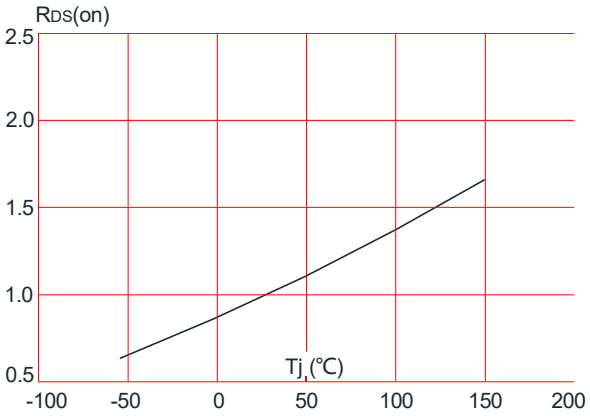


Figure 9: Maximum Safe Operating Area

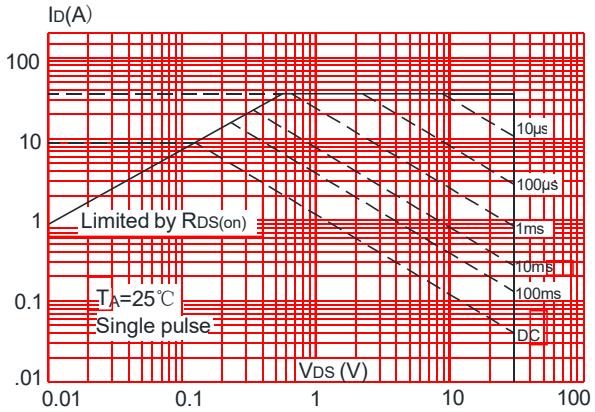


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

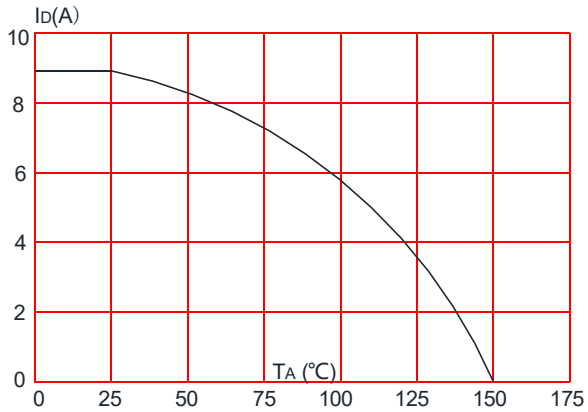
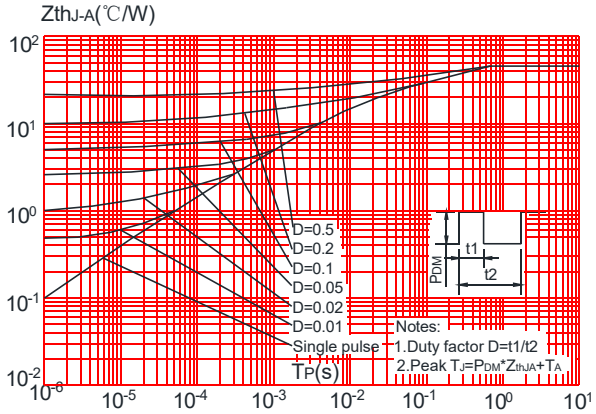


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

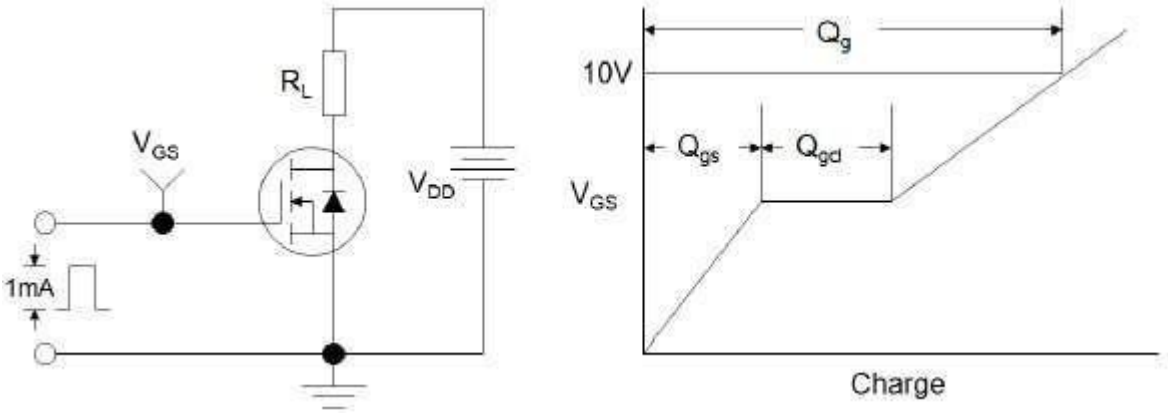


Figure1:Gate Charge Test Circuit & Waveform

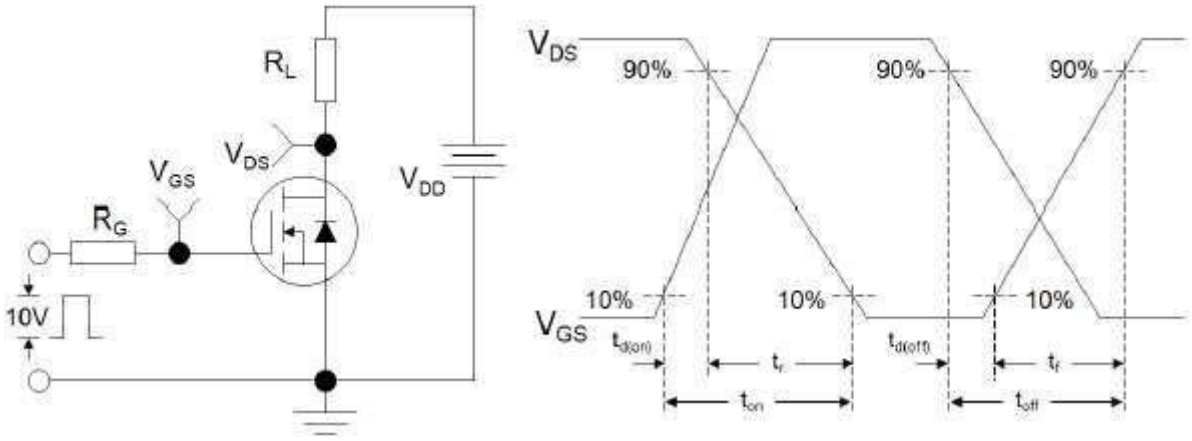


Figure 2: Resistive Switching Test Circuit & Waveforms

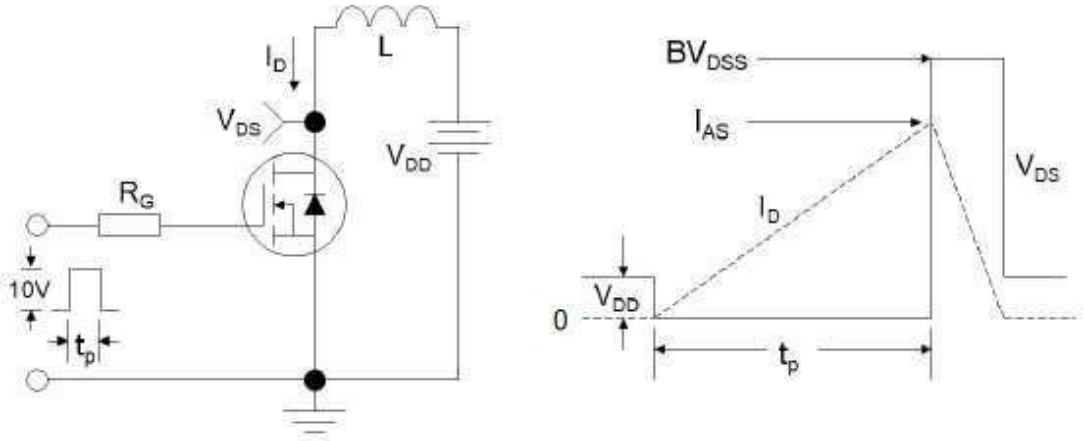
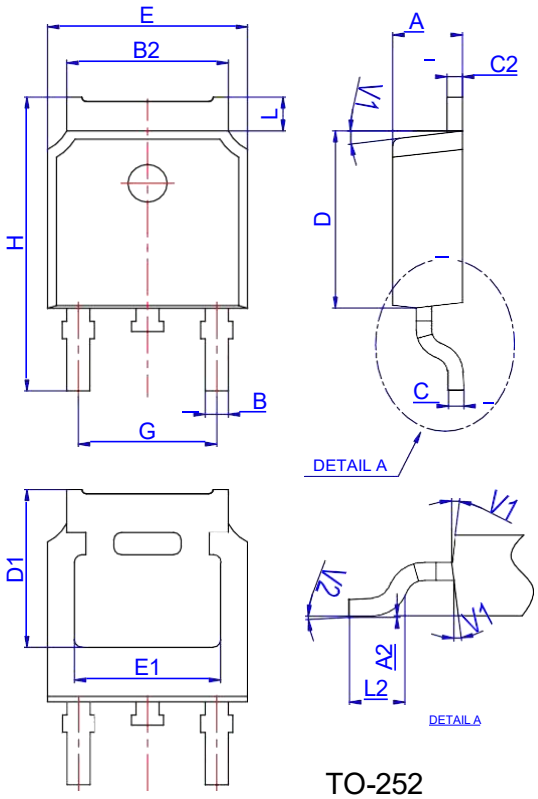


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

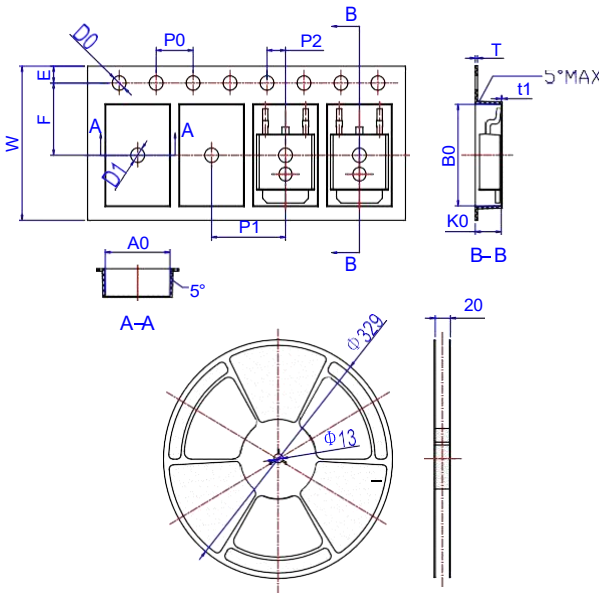
Package Mechanical Data TO 252 4R



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583